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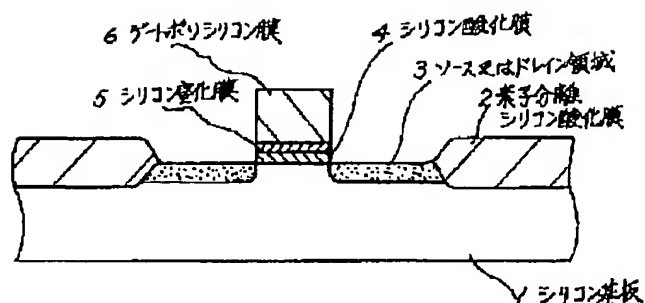
APPLICATION NUMBER : 03243359

APPLICANT : NEC CORP;

INVENTOR : MOGAMI TORU;

INT.CL. : H01L 29/784

TITLE : MOS TYPE FIELD EFFECT
TRANSISTOR AND ITS
MANUFACTURE



ABSTRACT : PURPOSE: To realize a surface channel type p⁺ polysilicon gate PMOS type field effect transistor which develops no punchthrough of baron and whose electric characteristics of device is the same as the case where a silicon oxide film is a gate insulating film.

CONSTITUTION: A gate insulating film is of a double-layer structure of a silicon nitride film 5 and a silicon oxide film 4, and the silicon nitride film 5 is located on the gate electrode side.

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